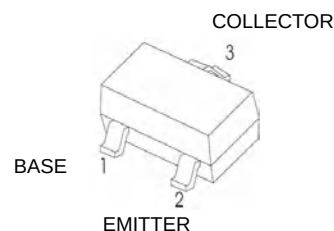




2SC2714 TRANSISTOR (NPN)

FEATURES

- Small reverse Transfer Capacitance: $C_{re}=0.7\text{pF}(\text{typ.})$
- Low Noise Figure: $NF=2.5\text{dB}(\text{typ.}) (f=100\text{MHz})$



SOT-23

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current -Continuous	20	mA
P_C	Collector Power Dissipation	100	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	1000	$^\circ\text{C/W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

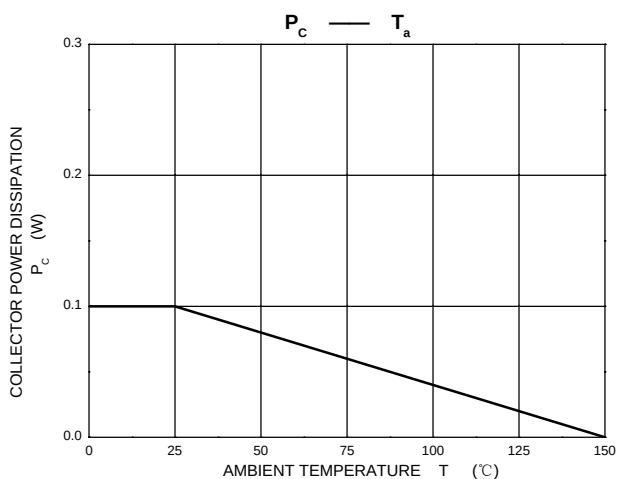
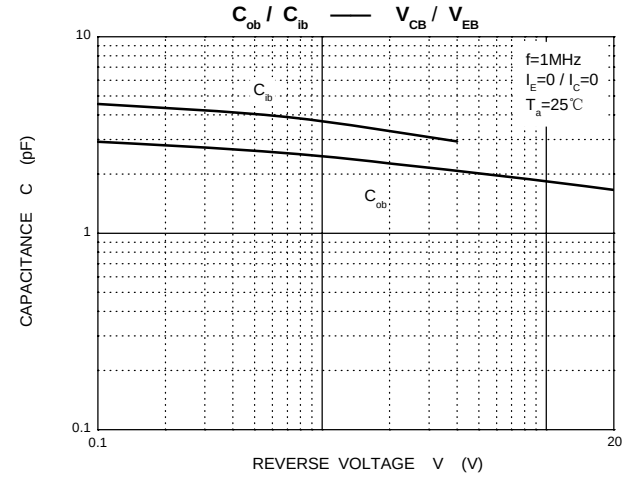
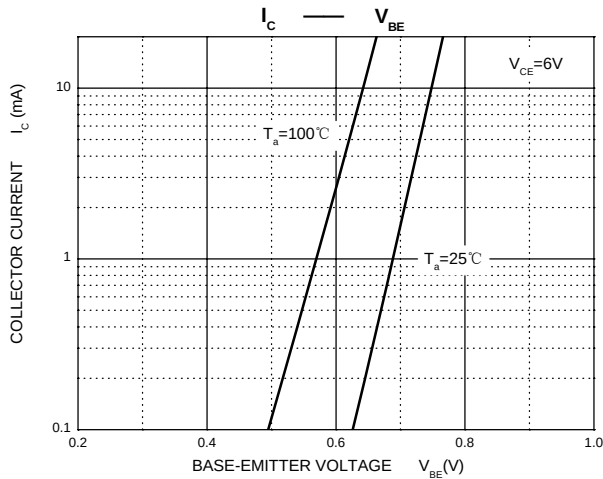
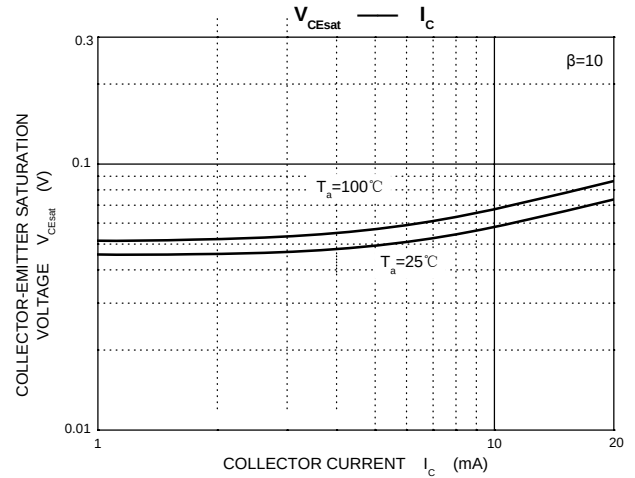
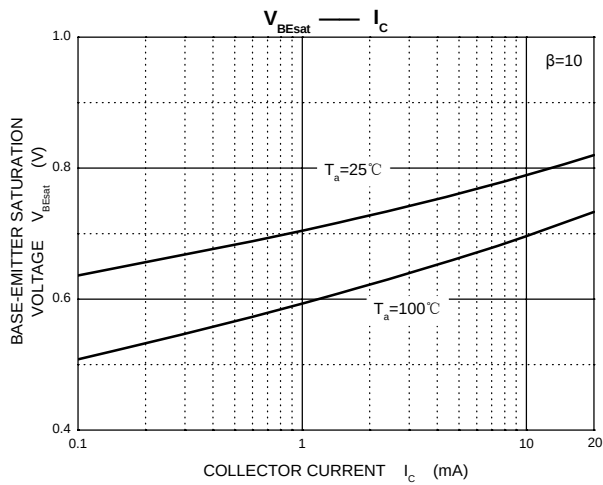
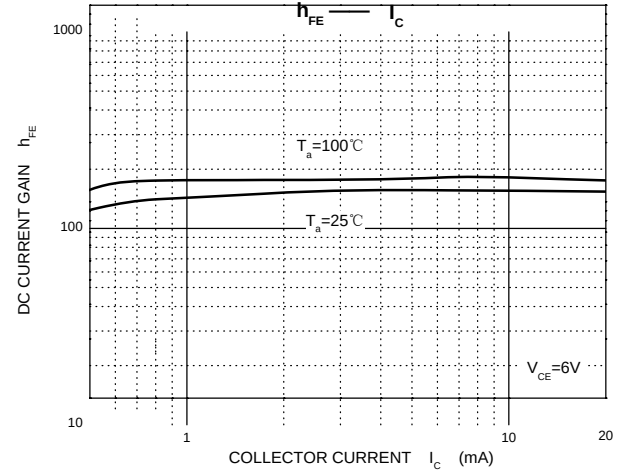
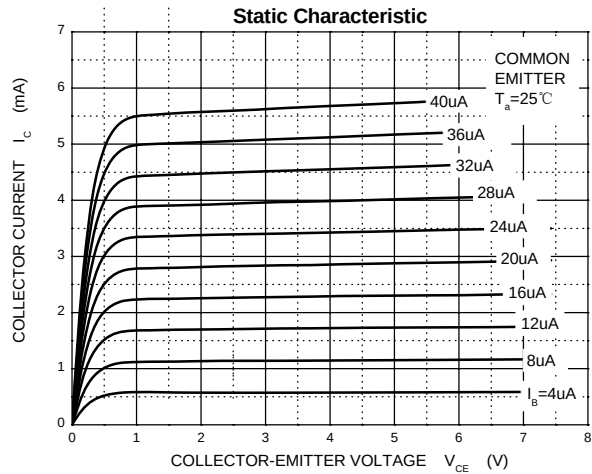
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=18\text{V}, I_E=0$			0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.5	μA
DC current gain	h_{FE}	$V_{CE}=6\text{V}, I_C=1\text{mA}$	40		200	
Transition frequency	f_T	$V_{CE}=6\text{V}, I_C=1\text{mA}$		550		MHz
Reverse Transfer capacitance	C_{re}	$V_{CB}=6\text{V}, I_E=0, f=1\text{MHz}$		0.7		pF
Noise figure	NF	$V_{CE}=6\text{V}, I_C=1\text{mA}, f=100\text{MHz}$		2.5	5	dB

CLASSIFICATION OF h_{FE}

Rank	R	O	Y
Range	40-80	70-140	100-200
Marking	QR	QO	QY



Typical Characteristics

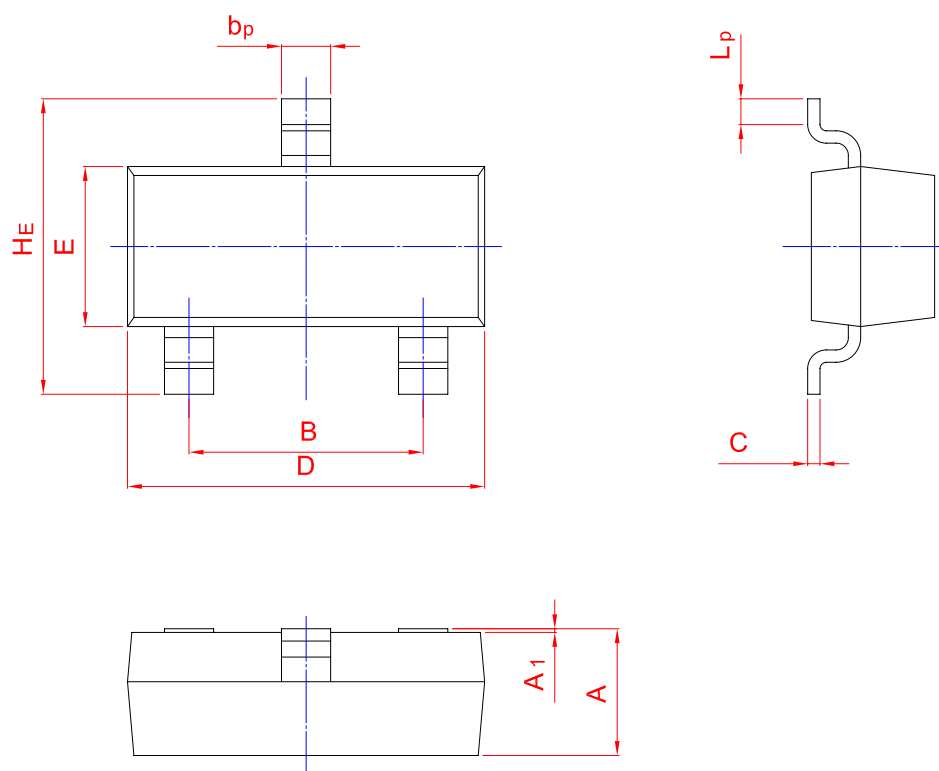




PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20